

## **Abstract Amendments**

Please replace the Abstract of the with the following new Abstract, marked up to show changes made relative to the immediate prior version:

A method for fabricating a high-voltage transistor with an extended drain region ~~comprises~~ includes forming an epitaxial layer on a substrate, the epitaxial layer and the substrate being of a first conductivity type; then etching the epitaxial layer to form a pair of spaced-apart trenches that define first and second sidewall portions of the epitaxial layer. A dielectric layer is formed that partially fills each of the trenches, covering the first and second sidewall portions. The remaining portions of the trenches are then filled with a conductive material to form first and second field plate members that are insulated from the substrate and the epitaxial layer. It is emphasized that this abstract is provided to comply with the rules requiring an abstract that will allow a searcher or other reader to quickly ascertain the subject matter of the technical disclosure. It is submitted with the understanding that it will not be used to interpret or limit the scope or meaning of the claims. 37 CFR 1.72(b).